

CLAIMS:

1. A semiconductor device comprising:
an inductor provided with a conductor interconnection formed spirally on a semiconductor substrate; and
a shield that is provided with a continuous conductor interconnection provided along the outer periphery of the spiral pattern of the inductor with opening a portion of the conductor interconnection, and that is electrically connected to ground potential.

2. A semiconductor device according to Claim 1, wherein an interconnection width of the shield and a distance between the shield and the outer border of the interconnection of the inductor each are at least equal in size to a spacing of the spiral pattern of the inductor.

3. A semiconductor device according to Claim 1, further comprising: a plurality of interconnection layers formed on the semiconductor substrate, wherein the inductor is formed in any one of these interconnection layers; and the shield is formed in the same interconnection layer as and/or a different interconnection layer from the interconnection layer in which the inductor is formed.

4. A semiconductor device comprising:
an inductor provided with a conductor interconnection formed spirally on a semiconductor substrate; and
a shield that is provided with a continuous conductor interconnection provided along the inner periphery of the spiral

pattern of the inductor with opening a portion of the conductor interconnection, and that is electrically connected to ground potential.

5. A semiconductor device according to Claim 4, wherein a interconnection width of the shield is at most equal in size to a interconnection width of the inductor.